

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled).
2. (Currently Amended) The electro-optical device according to claim 415, the multi-layered film being formed of a light-absorbing film as a bottom layer and a light-reflecting film as a top layer.
3. (Withdrawn-Currently Amended) The electro-optical device according to claim 415,
one of the pair of electrodes forming each of the storage capacitors forms part of a capacitor line formed in the second direction; and
the capacitor line being formed of a multi-layered film containing a low resistance film.
4. (Currently Amended) The electro-optical device according to claim 415, the multi-layered film being formed together with the data lines as the same film.
5. (Currently Amended) The electro-optical device according to claim 415, the low resistance film being made of aluminum.
6. (Currently Amended) The electro-optical device according to claim 415, each of the thin film transistors comprising:
a semiconductor layer including a channel region extending in the longitudinal direction and channel adjacent regions extending in the longitudinal direction further from the channel region, and a light-shielding portion is provided at both sides of the channel region.
7. (Original) The electro-optical device according to claim 6, each of the scanning lines comprising:

a main portion extending in a direction intersecting with the longitudinal direction and including a gate electrode of the thin film transistor overlapping with the channel region when viewed from the top; and horizontal projections extending in the longitudinal direction from the main portion at both sides of the channel region when viewed from the top so as to form the light-shielding portion.

8. (Original) The electro-optical device according to claim 7, the main portion at which the gate electrode being provided is formed wider.

9. (Original) The electro-optical device according to claim 7, the horizontal projections extending from both sides of the channel adjacent regions that are positioned at source and drain sides of the channel region when viewed from the top.

10. (Currently Amended) The electro-optical device according to claim 415, each of the thin film transistors comprising:

a semiconductor layer including a channel region extending in the longitudinal direction;

an upper light-shielding film to cover the channel region of the thin film transistor at least from the top is provided; and

the upper light-shielding film being at least partially formed in a recessed shape, as viewed from the channel region, in cross section orthogonal to the longitudinal direction of the channel region.

11. (Original) The electro-optical device according to claim 7, the scanning line further comprising:

a vertical projection extending in the vertical direction of the substrate from the main portion at a position away from the channel region in the second direction by a predetermined distance.

12. (Original) The electro-optical device according to claim 11,:

a lower light-shielding film to cover the channel region at least from the bottom being further provided on the substrate; and

the top of the vertical projection being in contact with the lower light-shielding film.

13. (Currently Amended) The electro-optical device according to claim 4, ~~15~~,

each of the thin film transistors including a semiconductor layer including a channel region extending in the first direction;

each of the scanning lines including a main portion having a gate electrode of the thin film transistor disposed to face the channel region with a gate insulating film therebetween and extending in the second direction intersecting with the first direction when viewed from the top; and

the main portion being disposed in a groove formed in the substrate, and also including an in-groove portion to cover at least part of the channel region from the sides.

14. (Currently Amended) The electro-optical device according to claim 4, ~~15~~,

at least part of the scanning lines, the data lines, the pair of electrodes forming the storage capacitor, and the shielding layer being formed of a light-shielding material; and

said at least part of the scanning lines, the data lines, the pair of electrodes forming the storage capacitor, and the shielding layer forming a built-in light-shielding film in a laminated structure.

15. (Original) An electro-optical device, comprising:

data lines extending in a first direction above a substrate;

scanning lines extending in a second direction and intersecting with the data lines;

pixel electrodes and thin film transistors disposed corresponding to intersections of the data lines and the scanning lines; storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

a light-shielding film disposed between the data lines and the pixel electrodes, one of a pair of electrodes forming the storage capacitor being formed of a multi-layered film containing a low resistance film.

16. (Currently Amended) An electronic apparatus, comprising:

an electro-optical device, said electro-optical device including as part of a laminated structure:

data lines extending in a first direction above a substrate;

scanning lines extending in a second direction and intersecting with the data lines;

pixel electrodes and thin film transistors disposed corresponding to intersections of the data lines and the scanning lines;

storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

a shielding layer light-shielding film disposed between the data lines and the pixel electrodes,

one of a pair of electrodes forming the storage capacitor being formed of a multi-layered film containing a low resistance film.

17. (New) The electro-optical device according to claim 2, the multi-layered film being together with the data lines as the same film.

18. (New) An electro-optical device, comprising:

data lines extending in a first direction above a substrate;

scanning lines extending in a second direction and intersecting with the data lines;

pixel electrodes and thin film transistors disposed corresponding to intersections of the data lines and the scanning lines;

storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

a shielding layer disposed between the data lines and the pixel electrodes, one of a pair of electrodes forming each of the storage capacitors being formed of a multi-layered film containing a low resistance film, and

each of the thin film transistors comprising:

 a semiconductor layer including a channel region extending in the longitudinal direction and channel adjacent regions extending in the longitudinal direction further from the channel region, and a light-shielding portion is provided at both sides of the channel region.

19. (New) An electro-optical device, comprising:

 data lines extending in a first direction above a substrate;
 scanning lines extending in a second direction and intersecting with the data lines;

 pixel electrodes and thin film transistors disposed corresponding to intersections of the data lines and the scanning lines;

 storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

 a shielding layer disposed between the data lines and the pixel electrodes, one of a pair of electrodes forming each of the storage capacitors being formed of a multi-layered film containing a low resistance film, and

each of the thin film transistors comprising:

 a semiconductor layer including a channel region extending in the longitudinal direction;

 an upper light-shielding film to cover the channel region of the thin film transistor at least from the top is provided; and

 the upper light-shielding film being at least partially formed in a recessed shape, as viewed from the channel region, in cross section orthogonal to the longitudinal direction of the channel region.

20. (New) An electro-optical device, comprising:

 data lines extending in a first direction above a substrate;

 scanning lines extending in a second direction and intersecting with the data lines;

 pixel electrodes and thin film transistors disposed corresponding to intersections of the data lines and the scanning lines;

 storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

 a shielding layer disposed between the data lines and the pixel electrodes,

 one of a pair of electrodes forming each of the storage capacitors being formed of a multi-layered film containing a low resistance film,

 each of the thin film transistors including a semiconductor layer including a channel region extending in the first direction,

 each of the scanning lines including a main portion having a gate electrode of the thin film transistor disposed to face the channel region with a gate insulating film therebetween and extending in the second direction intersecting with the first direction when viewed from the top, and

the main portion being disposed in a groove formed in the substrate, and also including an in-groove portion to cover at least part of the channel region from the sides.

21. (New) An electro-optical device, comprising:

data lines extending in a first direction above a substrate;

scanning lines extending in a second direction and intersecting with the data lines;

pixel electrodes and thin film transistors disposed corresponding to intersections of the data lines and the scanning lines;

storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

a shielding layer disposed between the data lines and the pixel electrodes, one of a pair of electrodes forming each of the storage capacitors being formed of a multi-layered film containing a low resistance film,

at least part of the scanning lines, the data lines, the pair of electrodes forming the storage capacitor, and the shielding layer being formed of a light-shielding material, and said at least part of the scanning lines, the data lines, the pair of electrodes forming the storage capacitor, and the shielding layer forming a built-in light-shielding film in a laminated structure.